

SEMiX 904GB126HDs



Trench IGBT Modules

SEMiX 904GB126HDs

Preliminary Data

Features

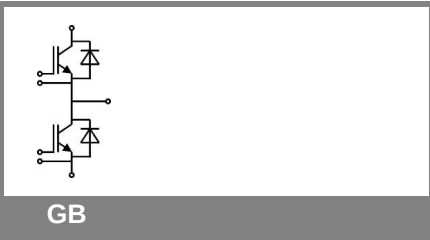
- Homogeneous Si
- Trench = Trenchgate technology
- $V_{CE(sat)}$ with positive temperature coefficient
- High short circuit capability

Typical Applications

- AC inverter drives
- UPS
- Electronic Welding

Remarks

- Case temperatur limited to $T_C=125^{\circ}C$ max.



Characteristics					
Symbol	Conditions	min.	typ.	max.	Units
Inverse Diode					
$V_F = V_{EC}$	$I_{Fnom} = 600\text{ A}; V_{GE} = 0\text{ V}$ $T_j = 25\text{ }^{\circ}C_{chiplev.}$ $T_j = 125\text{ }^{\circ}C_{chiplev.}$		1,6 1,6	1,8 1,8	V V
V_{F0}	$T_j = 25\text{ }^{\circ}C$ $T_j = 125\text{ }^{\circ}C$		1 0,8	1,1 0,9	V V
r_F	$T_j = 25\text{ }^{\circ}C$ $T_j = 125\text{ }^{\circ}C$		1 1,3	1,2 1,5	mΩ mΩ
I_{RRM} Q_{rr} E_{rr}	$I_{Fnom} = 600\text{ A}$ $di/dt = 8400\text{ A}/\mu s$ $V_{GE} = -15\text{ V}; V_{CC} = 600\text{ V}$ $T_j = 125\text{ }^{\circ}C$		625 165 75		A μC mJ
$R_{th(j-c)D}$	per diode			0,081	K/W
Module					
L_{CE}			22		nH
$R_{CC'+EE'}$	res., terminal-chip $T_{case} = 25\text{ }^{\circ}C$ $T_{case} = 125\text{ }^{\circ}C$		0,7 1		mΩ mΩ
$R_{th(c-s)}$	per module		0,03		K/W
M_s	to heat sink (M5)	3		5	Nm
M_t	to terminals (M6)	2,5		5	Nm
w				400	g
Temperature sensor					
R_{100} $B_{100/125}$	$T_c = 100^{\circ}C$ ($R_{25} = 5\text{ k}\Omega$) $R(T) = R_{100} \exp[B_{100/125} (1/T - 1/T_{100})]$ $T[K]$		0,493±5% 3550±2%		kΩ K

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.

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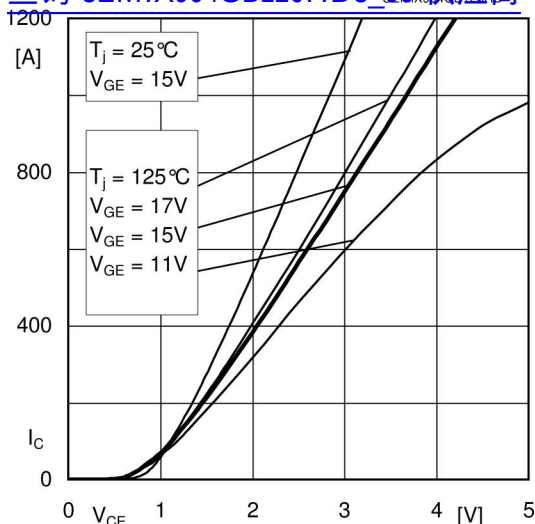


Fig. 1 Typ. output characteristic, inclusive $R_{CC'+EE'}$

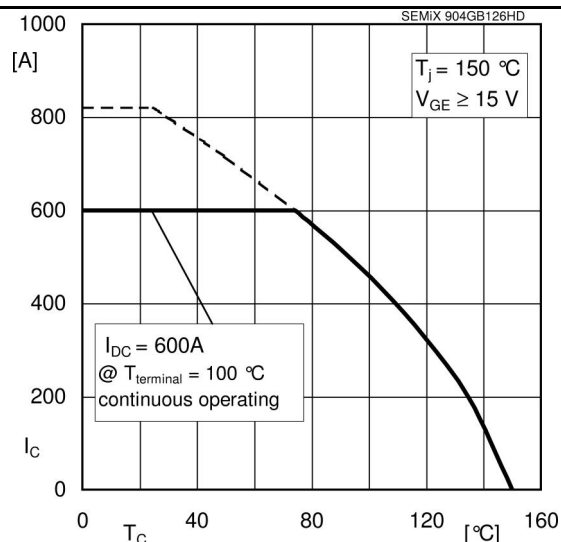


Fig. 2 Rated current vs. temperature $I_C = f(T_C)$

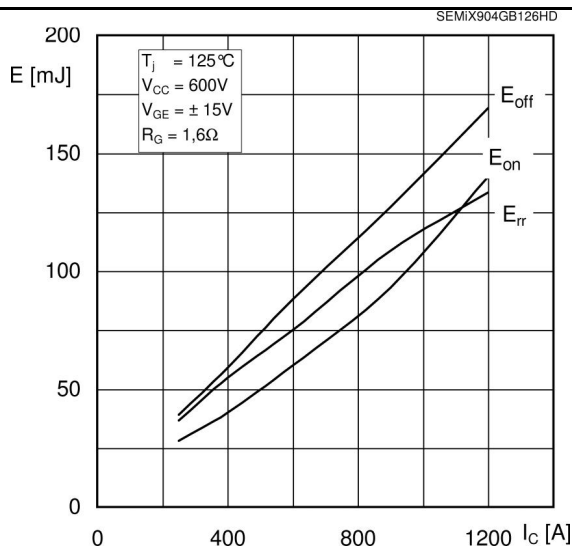


Fig. 3 Typ. turn-on /off energy = $f(I_C)$

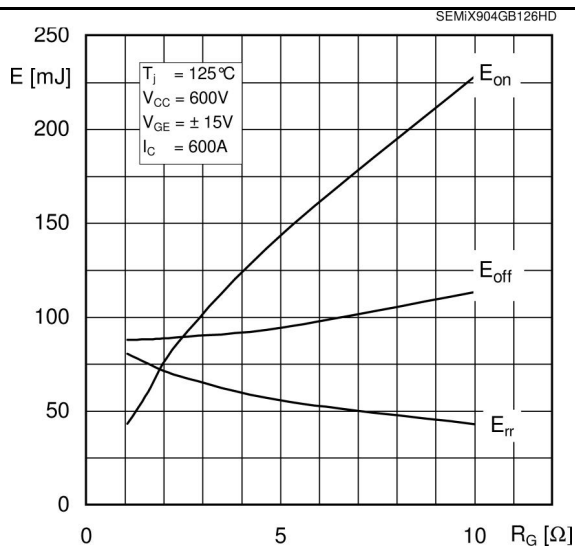


Fig. 4 Typ. turn-on /off energy = $f(R_G)$

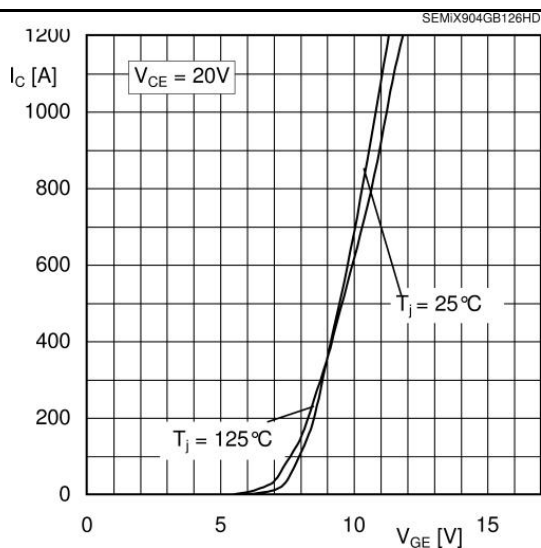


Fig. 5 Typ. transfer characteristic

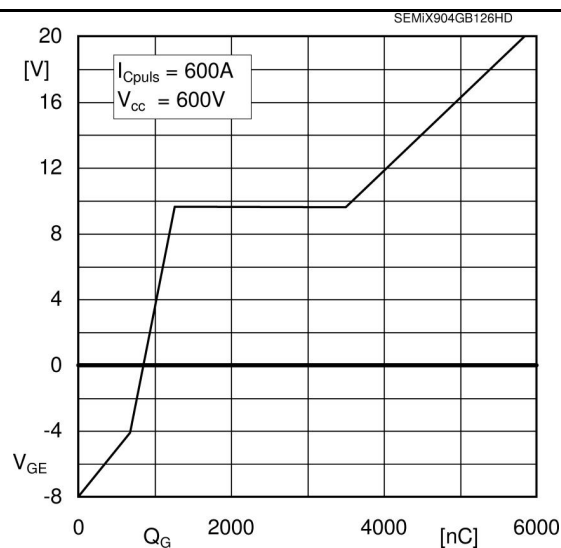


Fig. 6 Typ. gate charge characteristic

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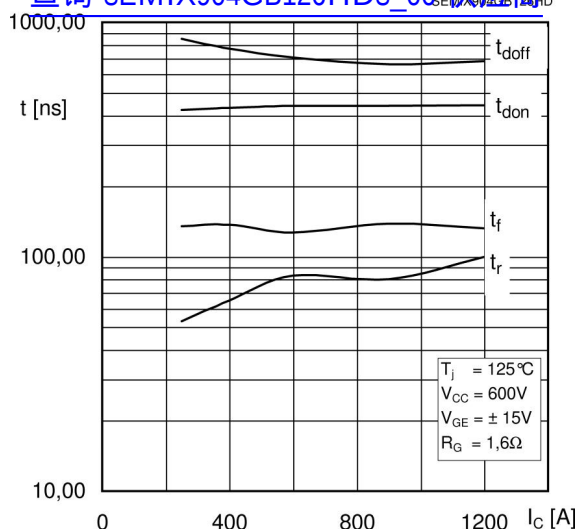


Fig. 7 Typ. switching times vs. I_C

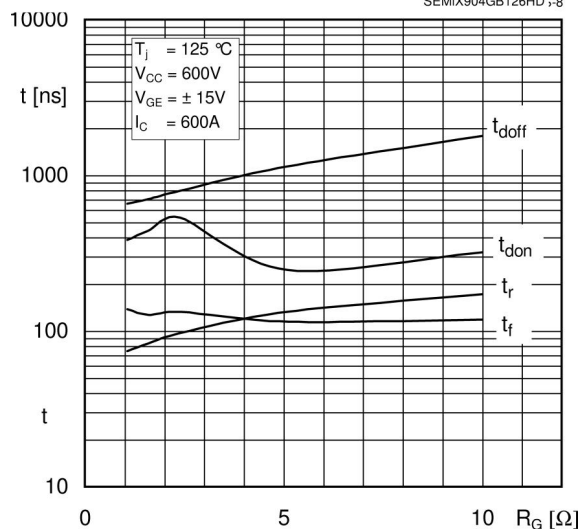


Fig. 8 Typ. switching times vs. gate resistor R_G

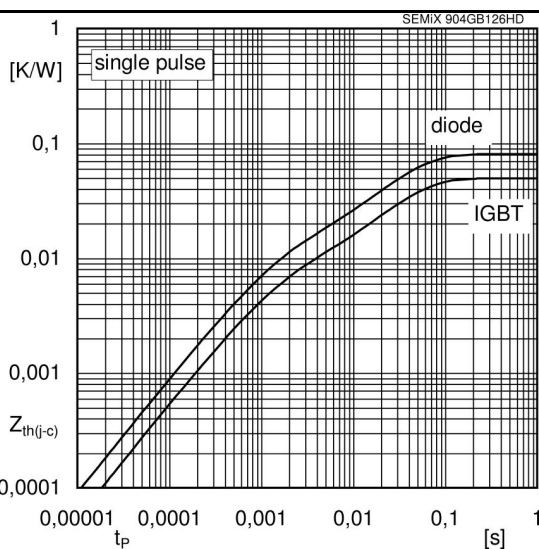


Fig. 9 Typ. transient thermal impedance

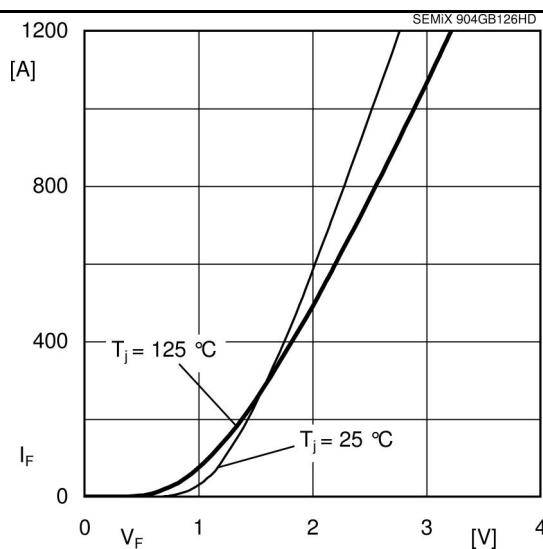


Fig. 10 Typ. CAL diode forward char., incl. $R_{CC+EE'}$

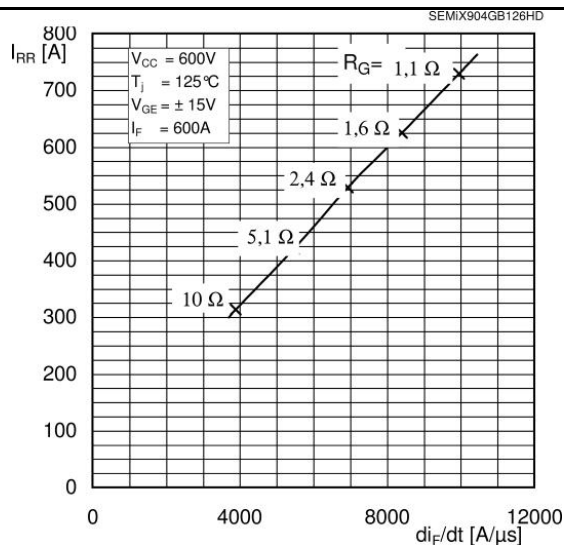


Fig. 11 Typ. CAL diode peak reverse recovery current

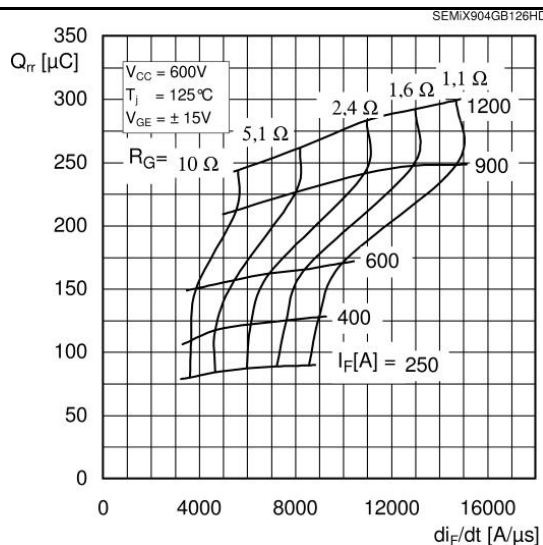
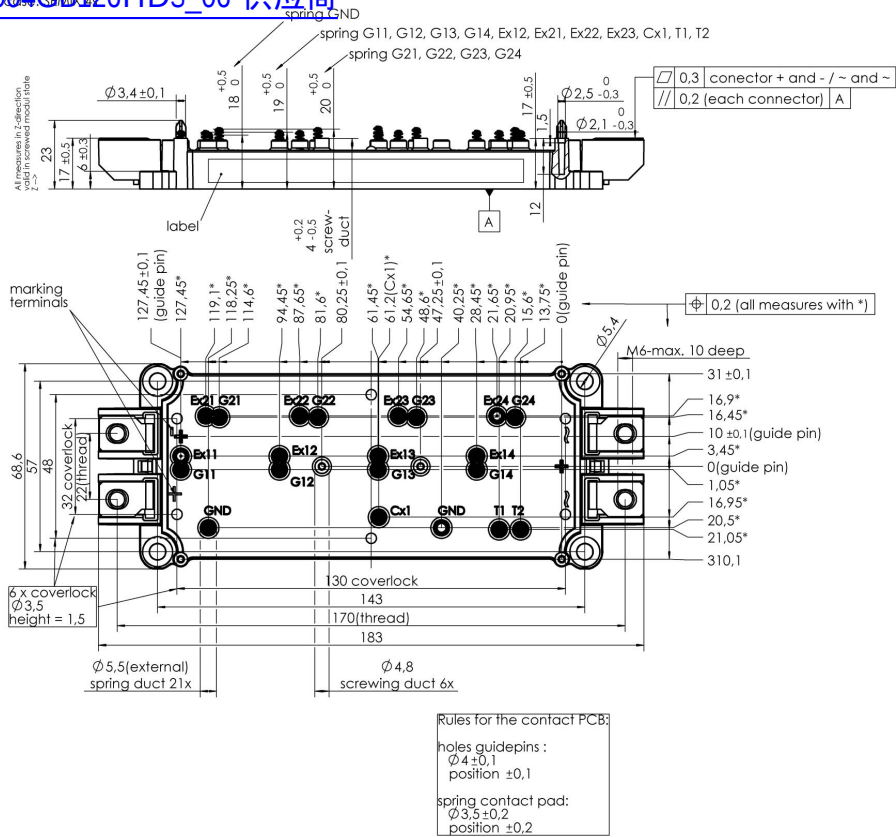


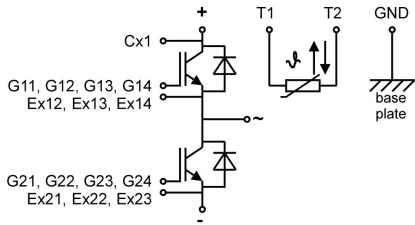
Fig. 12 Typ. CAL diode recovery charge

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Case SEMiX 4s



Pinout

GB